The first-principles study of nH-V_{sn} complex impurities effects in p-

type SnO monolayer

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Fig. S1 (a) four initial positions for H atom in H_i, (b) three initial positions for H atom in H-V_{Sn}.

Table. S1 The total energies in different charge states for four H_i initial positions in Fig. S1(a) and three H-V_{Sn} initial positions in Fig. S1(b) after relax.

	total energy(eV) for H _i				total energy(eV) for H-V _{sn}		
	1	2	3	4	1	2	3
0	-364.8996	-364.9157	-364.1463	-365.1927	-358.4531	-361.3345	-360.7871
-1	-365.9629	-367.1982	-366.5177	-366.0481	-361.3043	-364.0821	-363.4637
+1	-363.7871	-363.6252	-362.2930	-363.8007	-		



Fig. S2 Four initial positions for H atom in H-V₀.

Table. S2 The total	energies for fo	our H-V _O initial	positions in Fig.	S2 after relax.
	U	0	1 0	

position	total energy(eV)		
1	-357.0911		
2	-357.2232		
3	-356.3364		
4	-356.9181		



Fig .S3 The top and side view of four initial positions(top) for H atoms in $2H-V_0$ and their relax results(bottom) with total energies.



Fig. S4 The top and side view of three initial positions(top) for H atoms in $2H-V_{Sn}$ and their relax results(bottom) with total energies.



Fig. S5 The top and side view of three initial positions(top) for H atoms in $3H-V_{Sn}$ and their relax results(bottom) with total energies.



Fig. S6 The top and side view of four initial positions(top) for H atoms in $4H-V_{Sn}$ and their relax results(bottom) with total energies.